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Synthesis, Crystal Structure, and Electrical Conductivity of Pd-intercalated NbSe₂

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Abstract: New intercalated compounds Pd_xNbSe_2 (*x*=0-0.17) were synthesized *via* solid-state reaction. They possess the parent structure of 2H-NbSe₂ and crystalize in the hexagonal space group of P6₃/mmc. The intercalated Pd occupies the octahedral position in the van der Waals gaps of 2H-NbSe₂. Unit cell parameter *c* increases linearly with the Pd content, while *a* is nearly unchanged. The lattice parameter of Pd_{0.17}NbSe₂ (*a*=*b*=0.34611(2) nm, *c*= 1.27004(11) nm) is identified by single crystal X-ray diffraction. The intercalated Pd stabilizes the crystal structure of NbSe₂ by connecting the adjacent Nb-Se layers with [PdSe₆] octahedra and leads to the enhanced thermostability in air. Temperature dependence of electric resistivity reveals that the residual resistivity ratio of Pd_xNbSe₂ monotonically decreases with addition of the intercalated Pd content. The decreased superconducting critical temperature of Pd_xNbSe₂ indicates the suppression effect of Pd intercalation on the superconductivity in the host NbSe₂.

Key words: Pd_xNbSe₂; transition metal dichalcogenide; crystal structure; superconducting

Layered transition metal dichalcogenides (TMDs) with the general chemical formula MX_2 (M represents the transition metal and X is the chalcogen) have been widely studied due to their unique physicochemical properties and diverse applications^[1-5]. The metallic Group V B TMDs (where M = V, Nb and Ta) are prized for their fascinating electronic properties, such as charge density wave (CDW), superconductivity and Mott transition^[6-7]. Among them, 2H-NbSe₂ is featured with a high superconducting critical temperature (T_C) of ~7.3 K and a quasi-two-dimensional incommensurate charge density wave (ICDW) with a T_{CDW} of ~33 K^[8]. Because of the weak van der Waals (vdW) forces connected interlayers in the crystal structure, 2H-NbSe₂ can be intercalated by various guests, including atoms, ions, and molecules^[9].

Typically, the incorporation of guest metal atoms into the vdW gaps of TMDs could give rise to the crystallographic transformation and change of electronic structure in the intercalated compounds^[10]. Magnetic elements (Fe, Co) inserted into the vdW gaps of NbSe₂ resulted in the formation of superlattice^[11-12]. Alkali metal intercalation was found to remove the CDW instability in NbSe₂^[13]. Recently, noble metal, such as palladium (Pd), was applied to regulate the electronic structure efficiently for the host TMDs. Our group^[14] found that Pd modified the band structure of 2H-TaS₂ through Pd–S bonding to strengthen the interaction of adjacent Ta-S layers, which led to the enhanced conductivity in Pd_{0.10}TaS₂. Pd intercalation was reported to increase the effective electronphonon coupling in 2H-TaSe₂ and enhance the T_C in Pd_xTaSe₂^[15]. Considering that the crystal structure of 2H-NbSe₂ is identical to that of 2H-TaX₂ (X=S, Se), Pd intercalation should be applicable to 2H-NbSe₂ and tune the physical properties.

In this work, a series of new compounds Pd_xNbSe_2 (*x*=0~0.17) were synthesized and the crystal structure of $Pd_{0.17}NbSe_2$ was determined by single X-ray diffraction method in order to investigate the modification of crystal lattice and electrical conductivity in the Pd intercalated NbSe₂.

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1.1 Preparation of Pd_xNbSe₂

 Pd_xNbSe_2 crystals were prepared by solid-state reaction. Pd (99.99%), Nb (99.5%) and Se (99.99%) powders were mixed according to stoichiometric ratio, and ground. Then the mixtures were compacted into a pellet and heated in the evacuated (< 0.133 Pa) silica tube at 1173 K for 48 h. Subsequently, the as-obtained samples were reground, re-pelletized and held at 1173 K for 72 h. Then the samples were cooled down by quenching in water. High quality single crystal of $Pd_{0.17}NbSe_2$ was obtained by keeping $Pd_{0.17}NbSe_2$ powder with CsI (99.9%) at 1173 K for 1 d and slowly cooling down to 823 K for 3 d.

1.2 Characterization

Single crystal data collections of Pd_{0.17}NbSe₂ was conducted on a Bruker D8 QUEST diffractometer equipped with Mo Ka radiation at room temperature. The crystal structure determination and refinement were performed with the APEX3 program. The crystal structure of Pd_{0.17}NbSe₂ was drawn by using the VESTA program^[16]. The morphology and the composition of the Pd_{0.17}NbSe₂ were investigated by a scanning electron microscope (SEM, JSM6510) coupled with energy dispersive X-ray spectroscopy (EDXS, Oxford Instruments). The micro-structure of Pd_{0.17}NbSe₂ was uncovered by a high-resolution transmission electron microscope (HRTEM, JEM-2100F) and the selected area electron diffraction (SAED). The valence analysis of the Pd_{0.17}NbSe₂ was obtained from X-ray photoelectron spectroscope (XPS) carried out on the RBD upgraded PHI-5000C ESCA system (PerkinElmer) with Mg Ka radiation (hv=51253.6 eV). The binding energy in XPS analysis was corrected by referencing C 1s peak at 284.6 eV. Powder X-ray diffraction (PXRD) data of these Pd_xNbSe₂ samples were collected by using a Bruker D8QUEST diffractometer equipped with Cu K α radiation (λ =0.15405 nm). Thermogravimetric analysis (TG) and differential thermal analysis (DTA) were carried out on a NETZSCH STA449C thermal analyzer for investigating the thermal stability of Pd_{0.17}NbSe₂ and NbSe₂ in air. Resistivity of the as-obtained Pd_xNbSe₂ at different temperatures was executed on a Physical Properties Measurement System (PPMS, Quantum Design). A four-probe method was adopted for measurements of the resistance. More specifically, the powders were pressed into a disk. Silver paste and copper wire acted as the contact electrode and conduct wire, respectively. Normalized resistivity $(\rho/\rho_{300 \text{ K}})$ versus temperature curves were obtained via dividing the measured resistivity (ρ) by the resistivity value ($\rho_{300 \text{ K}}$) at room temperature.

2 Results and discussion

The crystal structure of $Pd_{0.17}NbSe_2$ identified by single crystal X-ray diffraction method is shown in Fig. 1(a-b), where the gray, blue, orange spheres represent Pd, Nb, and Se atoms, respectively. The crystal data and structure refinement of $Pd_{0.17}NbSe_2$ are given in Table 1. The fractional atomic coordinates and equivalent isotropic displacement parameters are summarized in Table S1. The atomic displacement parameters and the geometric pa rameters



Fig. 1 Crystal structure of Pd_{0.17}NbSe₂ along (a) the *bc*-plane and (b) the *ab*-plane, (c) [NbSe₆] triangular prism in Pd_{0.17}NbSe₂,
(d) [PdSe₆] octahedron in Pd_{0.17}NbSe₂

Table 1	Crystal	data	and	structure
refi	nement o	of Pd	0.17N	bSe ₂

Chemical formula	Pd _{0.17} NbSe ₂
$M_{ m r}/({ m g}\cdot{ m mol}^{-1})$	269.03
Crystal system	Hexagonal, P63/mmc
<i>a</i> , <i>c</i> /nm	0.34611(2), 1.27004(11)
V/nm ³	0.13176(2)
Ζ	2
Radiation type	Mo Kα, λ=0.071073 nm
Crystal color	Black
$ ho_{\rm c}/({\rm g\cdot cm}^{-3})$	6.781
μ/mm^{-1}	32.93
Crystal size/mm ³	0.01×0.01×0.003
Diffractometer	Bruker D8 QUEST
T_{\min}, T_{\max}	0.494, 0.746
No. of measured, independent and observed $[I > 2\sigma(I)]$ reflections	1480, 121, 103
$R_{ m int}$	0.053
$(\sin\theta/\lambda)_{\rm max}/{\rm nm}^{-1}$	7.55
R_1 , w R_2 , S ^{<i>a</i>}	0.019, 0.035, 1.14
No. of reflections	121
No. of parameters	9

 ${}^{a}R_{1}=\Sigma||F_{o}|-|F_{c}||/\Sigma|F_{o}|, \quad wR_{2}=[\Sigma w(F_{o}^{2}-F_{c}^{2})^{2}/\Sigma(wF_{o}^{2})^{2}]^{1/2}, \quad w=1/[\sigma^{2}(F_{o}^{2})+(aP)^{2}+bP], \text{ where } F_{o} \text{ is the observed structure factor, } F_{c} \text{ is the calculated structure factor, } \sigma \text{ is the standard deviation of } F_{c}^{2}, \text{ and } P=(F_{o}^{2}+2F_{c}^{2})/3. S=[\Sigma w(F_{o}^{2}-F_{c}^{2})^{2}/(n-p)]^{1/2}, \text{ where } n \text{ is the number of reflections and } p \text{ is the total number of parameters refined.}$

are shown in Table S2–S3. The space group of $Pd_{0.17}NbSe_2$ is determined to be $P6_3$ /mmc with lattice parameters of a=0.34611(2) nm, c=1.27004(11) nm. $Pd_{0.17}NbSe_2$ contains one independent Nb site (2b), one independent Se site (4f) and one independent Pd site (2a). $Pd_{0.17}NbSe_2$ consists of Nb-Se layer and Pd-Se layer, which are stacked alternately along *c* axis. Each Nb atom is coordinated by 6 Se atoms which formed a [NbSe₆] triangular prism (Fig. 1(c)). The length of Nb–Se bond in [NbSe₆] triangular prism is 0.26006(4) nm which is comparable to 0.25941(5) nm in NbSe₂^[17]. These [NbSe₆] triangular prisms are connected by edge-sharing to form the Nb-Se layer.

Each Pd atom is coordinated by 6 Se atoms to form $[PdSe_6]$ octahedron (Fig. 1(d)). The average length of Pd–Se bond in $[PdSe_6]$ octahedron is 0.25051(4) nm

which is comparable to 0.248602(0) nm of PdSe₂^[18]. These [PdSe₆] octahedra partially fill in the vdW gaps of NbSe₂, where the occupation of Pd sites is 17%.

The $Pd_{0.17}NbSe_2$ plate with the size about 5 µm was observed by SEM (Fig. 2(a)). The Pd atoms are in a homogenous dispersion in $Pd_{0.17}NbSe_2$, which is confirmed by the elemental mapping analysis of $Pd_{0.17}NbSe_2$. HRTEM image of $Pd_{0.17}NbSe_2$ (Fig. 2(b)) reveals that the lattice fringes with a spacing of 0.301 nm are assigned to (101) plane and (1T1) plane between which the angle is 60°. This result is also verified by the corresponding SAED.

XPS data was obtained to confirm the valence state variation of the elements in $Pd_{0.17}NbSe_2$. As displayed in Fig. 3(a), the Pd 3d region is the only difference between $Pd_{0.17}NbSe_2$ and $NbSe_2$. The Pd 3d region of



Fig. 2 (a) SEM images of Pd_{0.17}NbSe₂ and the corresponding elemental mapping analysis, and (b) HRTEM image of Pd_{0.17}NbSe₂ along [10T] zone axis with inset showing the corresponding SAED pattern



 $\label{eq:Fig.3} Fig. \ 3 \qquad XPS \ results \ of \ Pd_{0.17}NbSe_2 \ and \ NbSe_2 \\ (a) \ Survey \ spectra, \ (b) \ Pd \ 3d \ spectrum \ of \ Pd_{0.17}NbSe_2, \ (c) \ Se \ 3d \ spectrum, \ and \ (d) \ Nb \ 3d \ spectrum \\ \ Nb \ 3d \ spectrum \ spectrum$

Pd_{0.17}NbSe₂ shows two peaks, which locate at the binding energy of 341.95 eV (3d_{3/2}) and 336.70 eV (3d_{5/2}) (Fig. 3(b)). The valance state of Pd in Pd_{0.17}NbSe₂ is identified as +2 according to these two peaks^[14]. There are two peaks locating at 55.27 (Se 3d_{3/2}) and 54.50 eV (Se 3d_{5/2}) in the Se 3d region of Pd_{0.17}NbSe₂, similar to those in the Se 3d region of NbSe₂ (Se 3d_{3/2} at 55.25 eV and Se 3d_{5/2} at 54.49 eV) (Fig. 3(c)). Therefore, the valance state of Se in Pd_{0.17}NbSe₂ is considered as -2. The Nb 3d region shows a mixture of oxidation states because of the slightly oxidation of the samples (Fig. 3(d))^[19]. The peaks locating at 206.93 and 204.20 eV are attributed to the Nb-Se bonding in Pd_{0.17}NbSe₂. In comparison with these two peaks in pristine NbSe₂ (207.01 and 204.25 eV), there is a slight redshift in Pd_{0.17}NbSe₂, implying the partial reduction of Nb as a result of Pd intercalation^[14].

The intercalated amounts of Pd in NbSe₂ could be variable, resulting in the formation of a series of Pd_xNbSe₂. The powder XRD patterns of Pd_xNbSe₂ are displayed in Fig. 4(a), with the pristine NbSe₂ as reference. The peaks of Pd_{0.17}NbSe₂ are well matched to the simulated one obtained from single crystal data, which suggests a high degree of phase purity. The NbSe₂ still maintains its space group (P6₃/mmc) after Pd intercalation. The (004) peak gradually shifts to a lower angle compared with

2H-NbSe₂. Furthermore, the lattice parameter a undergoes a negligible change. In a sharp contrast, lattice parameter c increases remarkably because of Pd intercalation enlarging the interlayer space of NbSe₂ (Fig. 4(b)).

The influence of Pd intercalation on the thermostability of the samples was investigated. As clearly seen in Fig. 5(a), the weight of NbSe₂ begins to increase slightly at 559 K due to the formation of Nb₂Se₄O₁₃^[20]. Subsequently, TG curve of NbSe₂ suffers a dramatic decrease because of the complete oxidation of NbSe₂ to Nb₂O₅. However, the process of mass increase could not be found in Pd_{0.17}NbSe₂, suggesting that the intercalated Pd enhances the thermostability of NbSe₂ with a higher oxidizing temperature. According to DTA curves (Fig. 5(b)), the oxidizing temperature of Pd_{0.17}NbSe₂ is 608 K, higher than NbSe₂ (544 K). The enhanced thermostability in air could stem from the intercalated Pd which stabilizes the crystal structure of NbSe₂ by connecting the adjacent Nb-Se layers^[11,21-22].

The electrical conductivity of Pd_xNbSe_2 was measured by PPMS. The resistivity of Pd_xNbSe_2 increases with the rising temperature (Fig. S1) exhibiting metallic behavior. Moreover, the residual resistivity ratio (*RRR*) [(resistivity at 300 K)/(resistivity just above T_C)] for the $Pd_{0.17}NbSe_2$ is ~1.09, extremely lower than NbSe₂ (~7.67) (Fig. 6(a)).



Fig. 4 (a) Powder XRD patterns of Pd_xNbSe_2 (x=0, 0.05, 0.10, 0.15, 0.17), (b) composition dependence of the lattice parameters a and c for Pd_xNbSe_2 ($0 \le x \le 0.17$)



Fig. 5 (a) TG and (b) DTA curves of Pd_{0.17}NbSe₂ (blue) and NbSe₂ (red)



Fig. 6 (a) Temperature dependence of the RRR $(\rho/\rho_{300 \text{ K}})$ for Pd_xNbSe₂ ($0 \le x \le 0.17$) with inset showing enlarged temperature region f the superconducting transition, (b) composition dependence of $T_{\rm C}$

The poor RRR in Pd_{0.17}NbSe₂ indicates that the intercalated Pd may be an electronically disruptive dopant in NbSe₂, which is similar to the copper (Cu) in Cu_xNbSe₂ and the gallium (Ga) in Ga, NbSe₂^[8,23]. All of the Pd_xNbSe₂ samples exhibit a sharp decrease at low temperature region from 8 K to 2K, indicating that the superconductivity occurs in these samples. Fig. 6(b) shows that the $T_{\rm C}$ decreases with a higher intercalated amount of Pd (7.4 K for NbSe₂ and 2.7 K for Pd_{0.17}NbSe₂). Eventually, the zero resistivity cannot be observed at 2 K in Pd_{0.17}NbSe₂. Therefore, it declares that the intercalated Pd has a negative effect on the superconductivity in NbSe₂. Similar phenomena are also found in Cu_rNbSe₂, Ga_xNbSe₂, Fe_xNbSe₂ and Al_xNbSe₂^[8,23-24]. The reason for this might be that Pd intercalation disrupts the coherence of the CDW, and suppresses the pairing channel which contributes to the higher $T_{\rm C}$ in NbSe₂^[8].

3 Conclusions

In summary, we introduced noble metal Pd into the vdW gaps of NbSe₂, and synthesized a series of new intercalated compounds Pd_xNbSe₂. The Pd_{0.17}NbSe₂ crystalizes in hexagonal structure with cell parameter a= 0.34611(2) nm, c=1.27004(11) nm. The intercalated Pd stabilizes the crystal structure of NbSe₂ by connecting the adjacent Nb-Se layers with [PdSe₆] octahedra leading to

the enhanced thermostability in air. Pd_xNbSe_2 remains the metallic character, which is verified by the resistivity measurements. In addition, the incorporation of Pd decreases the T_C of NbSe₂, implying that Pd is negative for the superconductivity in NbSe₂.

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Pd 插层 NbSe2 化合物的制备、晶体结构和电学性质研究

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摘 要:通过固相反应法合成一系列插层化合物 Pd_xNbSe₂ (*x*=0~0.17)。它们与 2H-NbSe₂ 相同,属于六方晶格,空间 群为 P6₃/mmc。Pd 占据 NbSe₂ 层间的八面体空位。随着 Pd 含量的增加,晶格常数 *c* 线性增大,而 *a* 几乎不变。X 射线单晶衍射结果表明, Pd_{0.17}NbSe₂ 的晶格常数为 *a=b=*0.34611(2) nm, *c=*1.27004(11) nm。每个 Pd 原子与六个 Se 原子键合形成[PdSe₆]八面体来连接相邻的 Nb-Se 层,使晶体结构变得更加稳定,从而提高化合物的热稳定性。电学 测试表明,随着 Pd 含量的增加, Pd_xNbSe₂ 的剩余电阻比减小。此外,超导转变温度也随着 Pd 含量的增加而下降,说 明 Pd 的引入不利于 NbSe₂ 的超导态。

关 键 词: Pd_xNbSe₂; 过渡金属硫族化合物; 晶体结构; 超导

中图分类号: O782 文献标识码: A

Supporting information:

Synthesis, Crystal Structure, and Electrical Conductivity of Pd-intercalated NbSe₂

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Table S1 Fractional atomic coordinates and isotropic or equivalent isotropic displacement paramet	ers of Pd _{0.17} NbSe ₂
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Atom	Wyck. Site	x	у	Ζ	$U_{\rm iso}$ * or $U_{\rm eq}/{\rm nm}^2$	Occ.
Nb	2b	0	1	1/4	0.000075(2)	1
Se	4f	1/3	2/3	0.38104(5)	0.0000736(17)	1
Pd	2a	0	1	1/2	0.000059(11)	0.171(3)

Table S2 Atomic displacement parameters of Pd _{0.17} NbSe ₂						
	U_{11}/nm^2	U_{22}/nm^2	U_{33}/nm^2	U_{12}/nm^2	U_{13}/nm^2	U_{23}
Nb	0.000074(3)	0.000074(3)	0.000075(4)	0.0000372(13)	0	0
S	0.000064(2)	0.000064(2)	0.000094(3)	0.0000318(10)	0	0
Pd	0.000062(13)	0.000062(13)	0.000052(19)	0.000031(7)	0	0

Table S3 Geometric parameters for Pd_{0.17}NbSe₂

Bond	Distance/nm	Bond	Distance/nm
Nb1—Se2 ⁱ	0.26006(4)	Se2—Pd3 ^{viii}	0.25051(4)
Nb1—Se2 ⁱⁱ	0.26006(4)	Se2—Nb1 ^{viii}	0.26006(4)
Nb1—Se2 ⁱⁱⁱ	0.26006(4)	Se2—Nb1 ^{vii}	0.26006(4)
Nb1—Se2 ^{iv}	0.26006(4)	Pd3—Se2 ^{ix}	0.25051(4)
Nb1—Se2	0.26006(4)	Pd3—Se2 ^{iv}	0.25051(4)
Nb1—Se2 ^{v}	0.26006(4)	Pd3—Se2 ^x	0.25051(4)
Nb1—Pd3 ^{vi}	0.31751(3)	Pd3—Se2 ⁱ	0.25051(4)
Nb1—Pd3	0.31751(3)	Pd3—Se2 ^{xi}	0.25051(4)
Se2—Pd3 ^{vii}	0.25051(4)	Pd3—Nb1 ^{xi}	0.31751(3)
Se2—Pd3	0.25051(4)		
Bond	Angle/(°)	Bond	Angle/(°)
Se2 ⁱ —Nb1—Se2 ⁱⁱ	134.813 (8)	Pd3 ^{viii} —Se2—Nb1	133.822 (3)
Se2 ⁱ —Nb1—Se2 ⁱⁱⁱ	79.58 (2)	Nb1 ^{viii} —Se2—Nb1	83.434 (16)
Se2 ⁱⁱ —Nb1—Se2 ⁱⁱⁱ	83.434 (16)	Pd3 ^{vii} —Se2—Nb1 ^{vii}	76.881 (6)
Se2 ⁱ —Nb1—Se2 ^{iv}	83.434 (16)	Pd3—Se2—Nb1 ^{vii}	133.822 (3)
Se2 ⁱⁱ —Nb1—Se2 ^{iv}	79.58 (2)	Pd3 ^{viii} —Se2—Nb1 ^{vii}	133.822 (3)
Se2 ⁱⁱⁱ —Nb1—Se2 ^{iv}	134.813 (7)	Nb1 ^{viii} —Se2—Nb1 ^{vii}	83.434 (16)
Se2 ⁱ —Nb1—Se2	83.433 (16)	Nb1—Se2—Nb1 ^{vii}	83.434 (16)
Se2 ⁱⁱ —Nb1—Se2	134.812 (7)	Se2—Pd3—Se2 ^{ix}	92.612 (17)
Se2 ⁱⁱⁱ —Nb1—Se2	134.812 (8)	Se2—Pd3—Se2 ^{iv}	87.388 (17)
Se2 ^{iv} —Nb1—Se2	83.433 (16)	Se2 ^{ix} —Pd3—Se2 ^{iv}	180.0
Se2 ⁱ —Nb1—Se2 ^v	134.812 (8)	Se2—Pd3—Se2 ^x	92.612 (17)
Se2 ⁱⁱ —Nb1—Se2 ^v	83.434 (16)	Se2 ^{ix} —Pd3—Se2 ^x	87.388 (17)
Se2 ⁱⁱⁱ —Nb1—Se2 ^v	83.434 (16)	$Se2^{iv}$ —Pd3— $Se2^{x}$	92.612 (17)

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Bond	Angle/(°)	Bond	Angle/(°)
Se2 ^{iv} —Nb1—Se2 ^v	134.812 (8)	Se2—Pd3—Se2 ⁱ	87.388 (17)
Se2—Nb1—Se2 ^v	79.58 (2)	Se2 ^{ix} —Pd3—Se2 ⁱ	92.612 (17)
Se2 ⁱ —Nb1—Pd3 ^{vi}	129.790 (11)	Se2 ^{iv} —Pd3—Se2 ⁱ	87.388 (17)
Se2 ⁱⁱ —Nb1—Pd3 ^{vi}	50.210 (11)	Se2 ^x —Pd3—Se2 ⁱ	180.0
Se2 ⁱⁱⁱ —Nb1—Pd3 ^{vi}	50.210 (11)	Se2—Pd3—Se2 ^{xi}	180.0
Se2 ^{iv} —Nb1—Pd3 ^{vi}	129.790 (11)	Se2 ^{ix} —Pd3—Se2 ^{xi}	87.388 (17)
Se2—Nb1—Pd3 ^{vi}	129.790 (11)	Se2 ^{iv} —Pd3—Se2 ^{xi}	92.612 (17)
Se2 ^v —Nb1—Pd3 ^{vi}	50.210 (11)	Se2 ^x —Pd3—Se2 ^{xi}	87.388 (17)
Se2 ⁱ —Nb1—Pd3	50.210 (11)	Se2 ⁱ —Pd3—Se2 ^{xi}	92.612 (17)
Se2 ⁱⁱ —Nb1—Pd3	129.790 (11)	Se2—Pd3—Nb1	52.909 (12)
Se2 ⁱⁱⁱ —Nb1—Pd3	129.790 (11)	Se2 ^{ix} —Pd3—Nb1	127.092 (12)
Se2 ^{iv} —Nb1—Pd3	50.210 (11)	Se2 ^{iv} —Pd3—Nb1	52.908 (12)
Se2—Nb1—Pd3	50.210 (11)	Se2 ^x —Pd3—Nb1	127.092 (12)
Se2 ^v —Nb1—Pd3	129.790 (11)	Se2 ⁱ —Pd3—Nb1	52.908 (12)
Pd3 ^{vi} —Nb1—Pd3	180.0	Se2 ^{xi} —Pd3—Nb1	127.091 (12)
Pd3 ^{vii} —Se2—Pd3	87.388 (17)	Se2—Pd3—Nb1 ^{xi}	127.091 (12)
Pd3 ^{vii} —Se2—Pd3 ^{viii}	87.388 (17)	Se2 ^{ix} —Pd3—Nb1 ^{xi}	52.908 (12)
Pd3—Se2—Pd3 ^{viii}	87.388 (17)	Se2 ^{iv} —Pd3—Nb1 ^{xi}	127.092 (12)
Pd3 ^{vii} —Se2—Nb1 ^{viii}	133.822 (2)	Se2 ^x —Pd3—Nb1 ^{xi}	52.908 (12)
Pd3—Se2—Nb1 ^{viii}	133.822 (3)	Se2 ⁱ —Pd3—Nb1 ^{xi}	127.092 (12)
Pd3 ^{viii} —Se2—Nb1 ^{viii}	76.881 (6)	Se2 ^{xi} —Pd3—Nb1 ^{xi}	52.909 (12)
Pd3 ^{vii} —Se2—Nb1	133.822 (2)	Nb1—Pd3—Nb1 ^{xi}	180.0
Pd3—Se2—Nb1	76.881 (6)		

Symmetry codes: (i) *x*, *y*+1, *z*; (ii) *x*-1, *y*, *-z*+1/2; (iii) *x*, *y*+1, *-z*+1/2; (iv) *x*-1, *y*, *z*; (v) *x*, *y*, *-z*+1/2; (vi) *-x*, *-y*+2, *z*-1/2; (vii) *x*+1, *y*, *z*; (viii) *x*, *y*-1, *z*; (ix) *-x*, *-y*+2, *z*-1/2; (vii) *x*+1, *y*, *z*; (viii) *x*, *y*-1, *z*; (ix) *-x*, *-y*+2, *z*-1/2; (viii) *x*+1, *y*, *z*; (viii) *x*+1, *y*, *z*; (viii) *x*, *y*-1, *z*; (ix) *-x*, *-y*+2, *z*-1/2; (viii) *x*+1, *y*, *z*; (viii) *x*+1, *y*, *z*; (viii) *x*, *y*-1, *z*; (ix) *-x*, *-y*+2, *z*-1/2; (viii) *x*+1, *y*, *z*; (viii) *x*+1, *z*; (viii) *x*+1, *z*; (viii) *x*+1, *y*, *z*; (viii) *x*+1, *z*; (viii) *x*; (viii) *x*; (viii) *x*; (viii) *x*; (viii) *x*; (viii) *x*; (vi



Fig. S1 Temperature dependence of the resistivity for Pd_xNbSe_2 ($0 \le x \le 0.17$)